



IXFK32N100P Information

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For Reference Only

Part Number IXFK32N100P

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 1000V 32A TO-264

Package TO-264-3, TO-264AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IXFK32N100P Specifications

Manufacturer Part Number IXFK32N100P Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-264-3, TO-264AA Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ ImA Gate Charge (Qg) (Max) @ Vgs 225nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 14200pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 960W (Tc) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264AA, (IXFK)		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-264-3, TO-264AA Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1225nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 14200pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature 4-55°C ~ 150°C (TJ) Mounting Type Supplier Device Package TO-264AA (IXFK) Package / Case	Manufacturer Part Number	IXFK32N100P
Package TO-264-3, TO-264AA Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 225nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 14200pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 960W (Tc) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264AA	Manufacturer	IXYS
Package TO-264-3, TO-264AA Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 225nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 14200pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 960W (Tc) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264AA	Category	Discrete Semiconductor Products
Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 225nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1420pF @ 25V Vgs (Max) ±30V FET Feature Power Dissipation (Max) 960W (Tc) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 225nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1420pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 960W (Tc) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature 55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case	Package	TO-264-3, TO-264AA
Technology Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 6.5V @ ImA Gate Charge (Qg) (Max) @ Vgs 125nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Supplier Device Package TO-264AA (IXFK) Package / Case TO-264AA	Series	HiPerFET?, PolarP2?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package TO-264AA (IXFK) Package / Case 10V 14V 14V 10V 225nC @ 10V 14200pF @ 25V 25V 25NC @ 10V 14200pF @ 25V 25V 25NC @ 10V 14200pF @ 25V 25V 25V 25V 25V 25V 25V 25V	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature Supplier Device Package TO-264AA (IXFK) Package / Case 32A (Tc) 46A (IVF) 76-264AA (IXFK) 76-264AA (IXFK) 76-264AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 14200pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case	Drain to Source Voltage (Vdss)	1000V
Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 225nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 14200pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 960W (Tc) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Current - Continuous Drain (Id) @ 25°C	32A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 14200pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 14200pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Vgs(th) (Max) @ Id	6.5V @ 1mA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)960W (Tc)Rds On (Max) @ Id, Vgs320 mOhm @ 16A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-264AA (IXFK)Package / CaseTO-264-3, TO-264AA	Gate Charge (Qg) (Max) @ Vgs	225nC @ 10V
FET Feature - Power Dissipation (Max) 960W (Tc) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Input Capacitance (Ciss) (Max) @ Vds	14200pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs320 mOhm @ 16A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-264AA (IXFK)Package / CaseTO-264-3, TO-264AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Power Dissipation (Max)	960W (Tc)
Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Rds On (Max) @ Id, Vgs	320 mOhm @ 16A, 10V
Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-264-3, TO-264AA	Mounting Type	Through Hole
	Supplier Device Package	TO-264AA (IXFK)
Report errors?	Package / Case	TO-264-3, TO-264AA
		Report errors?

IXFK32N100P Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXFK32N100P Payment Methods



















IXFK32N100P Shipping Methods













If you have any question about IXFK32N100P, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com